- 24
 lution comprising at least gall
- 3. The process of claim 1, wherein the introduction of the solvent occurs while the solvent is substantially in liquid form.
- **4**. The process of claim **1**, wherein the high pressure apparatus comprises an autoclave.
- 5. The process of claim 1, further comprising purging or evacuation followed by back-filling the capsule prior to introducing the solvent.
- **6**. The process of claim **3**, further comprising introducing thermal energy into the capsule during the purging or evacuation followed by back-filling.
- 7. The process of claim 6, wherein the thermal energy provides a temperature between 25 and 500 degrees Celsius during the purging or evacuation followed by back-filling.
- **8**. The process of claim **5** further comprising performing a 15 purging or back-filling process of the capsule using solvent vapor.
- 9. The process of claim 1, wherein the high pressure apparatus has an inner diameter greater than 100 mm.
- **10**. The process of claim **9**, wherein the high pressure ²⁰ apparatus has an inner diameter greater than 150 mm.
- 11. The process of claim 10, wherein the high pressure apparatus has an inner diameter greater than 200 mm.
- 12. A process for growing a crystalline gallium-containing nitride, the process comprising:
 - providing an autoclave or a capsule comprising galliumcontaining feedstock in one zone and at least one seed in another zone;
 - while maintaining an elevated pressure within the autoclave or capsule, introducing a first solvent capable of forming a supercritical fluid into at least the one zone and the other zone;
 - processing one or more portions of the gallium-containing feedstock in the supercritical fluid to provide a super-

- critical solution comprising at least gallium containing species at a first temperature;
- growing crystalline gallium-containing nitride material from the supercritical solution on the seed at a second temperature, the second temperature being characterized to cause the gallium containing species to form the crystalline gallium containing nitride material on the seed;
- removing thermal energy from the autoclave or capsule to form a second solvent from the supercritical solution; and
- removing the second solvent from the autoclave or capsule through an outlet; and
- transferring the second solvent from the outlet to a purification process.
- 13. The process of claim 12 wherein the solvent capable of forming a supercritical fluid is introduced into the capsule at an elevated pressure of at least about seven (7) atmospheres.
- 14. The process of claim 12 further comprising transferring the second solvent from the outlet to a purification process to recycle the second solvent.
- 15. The process of claim 12 further comprising transferring the second solvent from the outlet to a purification process to recycle the second solvent; purifying the second solvent in the purification process to form a third solvent; and transferring the third solvent to the autoclave or capsule.
- **16**. The process of claim **15** wherein the third solvent is substantially the same as the first solvent.
- 17. The process of claim 12 wherein the second solvent comprises a hydrogen species, nitrogen species, one or more trace metals, and dissolved mineralizer.
- 18. The process of claim 12 wherein the first solvent is substantially NH₃.

* * * * *